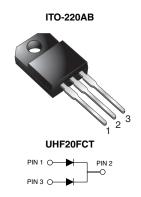


Vishay General Semiconductor

# **Dual Common-Cathode Ultrafast Recovery Rectifier**



PRIMARY CHARACTERISTICS					
I <sub>F(peak)</sub>	10 A x 2				
V <sub>RRM</sub>	300 V				
I <sub>FSM</sub>	180 A				
t <sub>rr</sub>	25 ns				
V <sub>F</sub> at I <sub>F</sub> = 10 A	0.85 V				
T <sub>J</sub> max.	175 °C				

#### **FEATURES**





- · Ultrafast recovery times
- · Soft recovery characteristics
- · Low switching losses, high efficiency



COMPLIANT

- High forward surge capability
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

#### **TYPICAL APPLICATIONS**

For use in high frequency power factor correctors, switching mode power supplies, freewheeling diodes and secondary dc-to-dc rectification application.

### **MECHANICAL DATA**

Case: ITO-220AB

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class

1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER		SYMBOL	UHF20FCT	UNIT		
Maximum repetitive peak reverse voltage		V <sub>RRM</sub>	300	V		
Maximum DC working forward current at $T_C = 125~^{\circ}C$	per device per diode	I <sub>F(peak)</sub>	20 10	Α		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	per diode	I <sub>FSM</sub>	180	А		
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min		V <sub>AC</sub>	1500	V		
Operating junction and storage temperature rar	nge	T <sub>J</sub> , T <sub>STG</sub>	- 55 to + 175	°C		

<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Maximum instantaneous forward voltage per diode <sup>(1)</sup>	$I_F = 5.0 \text{ A}$ $I_F = 10.0 \text{ A}$	T <sub>A</sub> = 25 °C	$V_{F}$	0.96 1.02	- 1.20	V
	I <sub>F</sub> = 5.0 A I <sub>F</sub> = 10.0 A	T <sub>A</sub> = 125 °C		0.77 0.85	-	
Maximum reverse current per diode (2)	V <sub>R</sub> = 300 V	T <sub>A</sub> = 25 °C T <sub>A</sub> = 125 °C	I <sub>R</sub>	0.06 25	5 150	μΑ

### **UHF20FCT**

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<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS	SYMBOL	TYP.	MAX.	UNIT	
Maximum reverse recovery time	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A},$ $I_{rr} = 0.25 \text{ A}$	t <sub>rr</sub>	20	25	ns	
Maximum reverse recovery time per diode	$I_F = 1.0 \text{ A, dI/dt} = 50 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, I}_{rr} = 0.1 \text{ I}_{RM}$	t <sub>rr</sub>	28	35	ns	
Typical softness factor (tb/ta)	I <sub>F</sub> = 10 A, dI/dt = 200 A/μs,	S	0.36	-	-	
Typical reverse recovery current	V <sub>R</sub> = 200 V, T <sub>J</sub> = 125 °C	I <sub>RM</sub>	7.0	-	Α	
Typical stored charge	per diode	$Q_{rr}$	160	•	nC	
Typical forward recovery time per diode	$I_F = 10 \text{ A}, \text{ dI/dt} = 80 \text{ A/}\mu\text{s}, \\ V_{FR} = 1.1 \text{ x } V_{Fmax}$	t <sub>fr</sub>	150	-	ns	

#### Notes:

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL UHF20FCT				
Typical thermal resistance per diode	R <sub>θJA</sub> <sup>(1)</sup> R <sub>θJC</sub> <sup>(2)</sup>	50 4.6	°C/W		

#### Notes:

- (1) Without heatsink, free air
- (2) With infinite heatsink

ORDERING INFORMATION (Example)							
PACKAGE PREFERRED P/N UNIT WEIGHT (g) PACKAGE CODE BASE QUANTITY DELIVERY MC							
ITO-220AB	UHF20FCT-E3/4W	1.74	4W	50/tube	Tube		

#### **RATINGS AND CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25 °C unless otherwise noted)

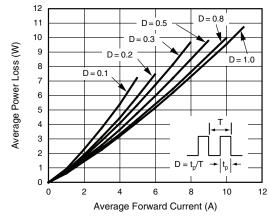


Figure 1. Forward Power Loss Characteristics Per Diode

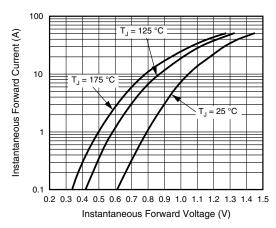


Figure 2. Typical Instantaneous Forward Characteristics Per Diode



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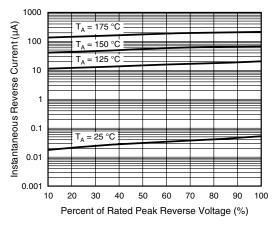


Figure 3. Typical Reverse Leakage Characteristics Per Diode

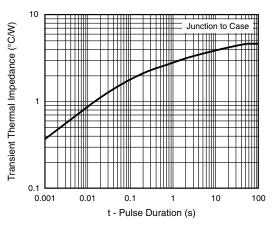


Figure 5. Typical Transient Thermal Impedance Per Diode

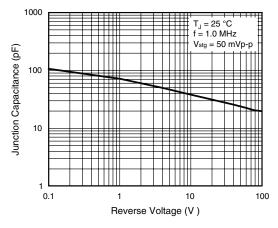
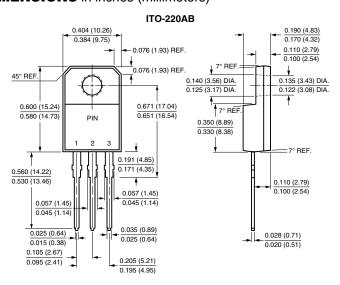


Figure 4. Typical Junction Capacitance Per Diode

### **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)





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